# Abstracts

## A Low Cost 3.6V Single-Supply GaAs Power Amplifier IC for the 1.9-GHz DECT System

*J. Griffiths and V. Sadhir. "A Low Cost 3.6V Single-Supply GaAs Power Amplifier IC for the 1.9-GHz DECT System." 1995 MTT-S International Microwave Symposium Digest 95.2 (1995 Vol. II [MWSYM]): 535-538.*

A GaAs power amplifier IC in a SOIC-16 plastic package has been developed for the 1.9 GHz Digital European Cordless Telephone (DECT) system. The power amplifier consists of two stages with all matching structures on chip and has a total area of 1.84 mm². At -2 dBm input power and 3.6 volts, the typical power amplifier achieves 26 dBm output power with 30% power-added efficiency, while operating from a single power supply in the SOIC-16 plastic package.

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